

	Type	Hits	Search Text	DBs
24	BRS	734	((open opened opening) adj drain) with (MOSFET FET transistor gate)	USPAT
25	BRS	579	(((open opened opening) adj drain) not (((open opened opening) adj drain) with (MOSFET FET transistor gate))) and substrate	USPAT
26	IS&R	3086	(257/107,133,335-339,341-343,350).CCLS.	USPAT; USOCR
27	BRS	3660	(open opened opening) adj drain	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	BRS	744	((open opened opening) adj drain) with (MOSFET FET transistor gate)	USPAT
29	BRS	599	(((open opened opening) adj drain) not (((open opened opening) adj drain) with (MOSFET FET transistor gate))) and substrate	USPAT
30	BRS	3852	(open opened opening) adj drain	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
31	IS&R	1140	(438/152,155,156,309,311).CCLS.	USPAT
32	IS&R	363	(438/152,155,156,309,311).CCLS.	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
33	BRS	147	((257/107,133,335-339,341-343,350).CCLS.) and ((electric adj static adj discharge) ESD (static adj charge))	USPAT
34	BRS	33	((257/107,133,335-339,341-343,350).CCLS.) and ((electric adj static adj discharge) ESD (static adj charge))	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
35	BRS	40	((438/152,155,156,309,311).CCLS.) and ((electric adj static adj discharge) ESD (static adj charge))	USPAT
36	BRS	18	((438/152,155,156,309,311).CCLS.) and ((electric adj static adj discharge) ESD (static adj charge))	US-PGPUB; USOCR; EPO; JPO; DERWENT; IBM_TDB
37	IS&R	3210	(257/107,133,335-339,341-343,350).CCLS.	USPAT; USOCR
38	IS&R	1709	(257/107,133,335-339,341-343,350).CCLS.	US-PGPUB; EPO; JPO; DERWENT; IBM_TDB